

film transistor, said [intrinsic or] at least substantially intrinsic semiconductor being produced by a process comprising the steps of:

forming on a surface an [intrinsic or] at least substantially intrinsic noncrystal semiconductor containing therein carbon, nitrogen and oxygen at a concentration of 5×10^{19} atoms·cm⁻³ or less respectively;

melting said [intrinsic or] at least substantially intrinsic noncrystal semiconductor by irradiating said [intrinsic or] at least substantially intrinsic noncrystal semiconductor with a laser beam or a light equivalent to the laser beam to crystallize said noncrystal semiconductor,

wherein the crystallized semiconductor has a peak of intensity of scattered light at a Raman shift of 512 cm⁻¹ or more in Raman spectroscopy thereof.

Claim 20, line 2, after "laser" delete " or YAG laser".

Please add new claims 21 and 22 as follows:

--21. The thin film transistor of claim 1 wherein the irradiation is carried out by YAG laser.

22. The thin film transistor of claim 18 wherein the irradiation is carried out by YAG laser.--

REMARKS

The Examiner's action of March 15, 1993 was received and carefully reviewed. Claims 4 and 18-20 were rejected under 35 U.S.C. §112, and claims 1-4 and 15-20 were rejected under 35 U.S.C. §103 over cited art discussed in detail below. Applicants respectfully request that the rejections of record be reconsidered and withdrawn. New claims 21 and 22 have added.